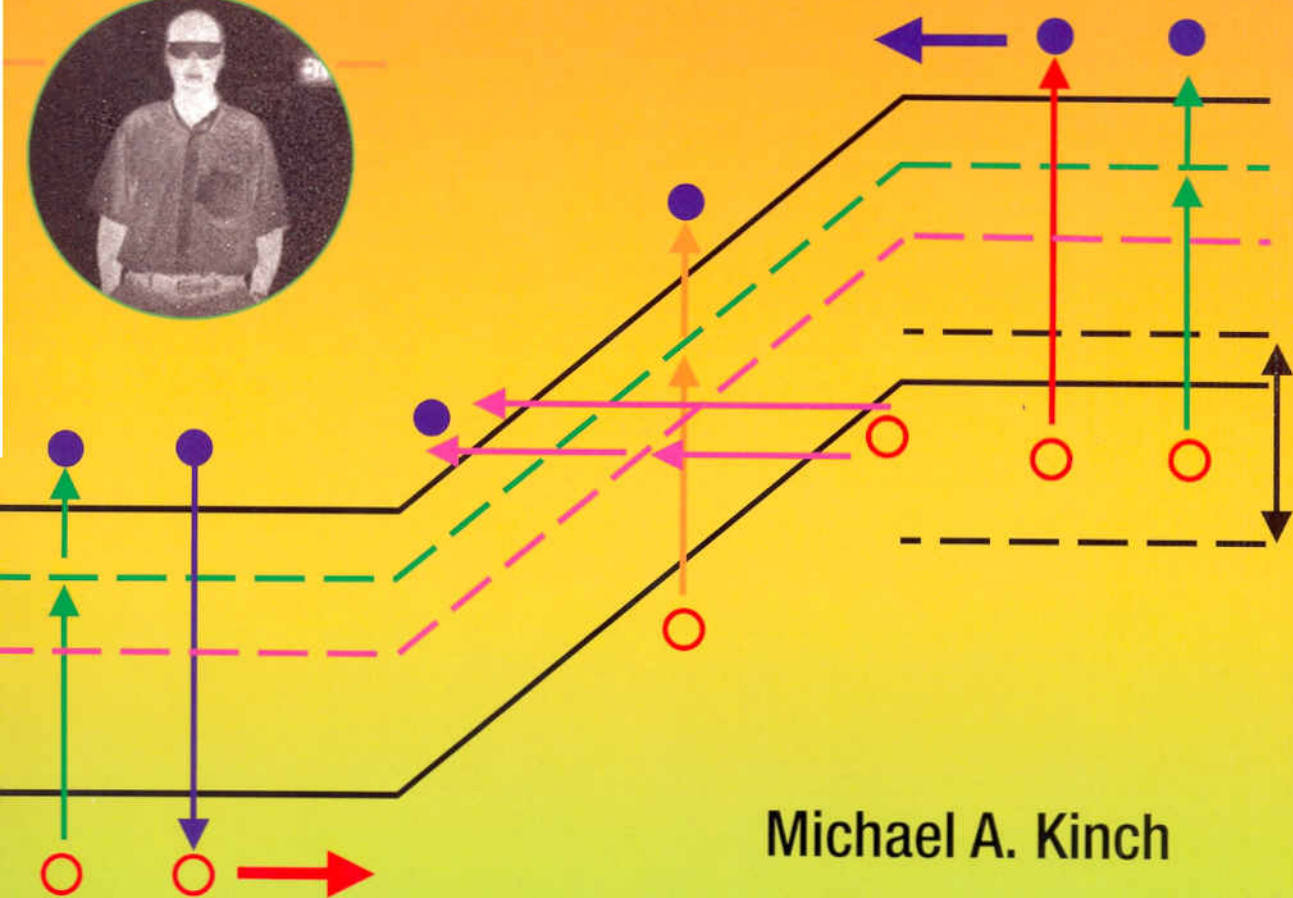




FUNDAMENTALS OF

Infrared Detector Materials



Michael A. Kinch

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Michael A. Kinch

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